New Jersey Semi-Conductor Products, Inc.

20 STERN AVE. SPRINGFIELD, NEW JERSEY 07081 U.S.A.



-30 - (-50) VOLTS -2 AMP, 10 WATTS

# VERY HIGH GAIN PNP POWER DARLINGTON TRANSISTORS

COMPLEMENTARY TO THE D40K SERIES



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#### Applications:

- Driver
- Regulator
- Touch Switch
- I.C. Driver
- Capacitor Multiplier
- Audio Output
- Relay Substitute
- Oscillator
- Servo-Amplifier

RATING	SYMBOL	D41K1,3	D41K2,4	UNITS Volts	
Collector-Emitter Voltage	VCEO	-30	-50		
Collector-Emitter Voltage	VCES	-13	-13	Volts	
Emitter Base Voltage	VEBO	-30	-50	Volts	
Collector Current — Continuous Peak <sup>(1)</sup>	IC ICM	-2 -3	-2 -3	AA	
Base Current — Continuous	<sup>I</sup> B	.2	.2	A	
Total Power Dissipation @ $T_A = 25^{\circ}C$ @ $T_C = 25^{\circ}C$	PD	-1.67 -10	-1.67 -10	Watts	
Operating and Storage Junction Temperature Range	TJ, TSTG	-55 to +150	-55 to +150	°C	

### maximum ratings (T<sub>A</sub> = 25°C) (unless otherwise specified)

#### thermal characteristics

Thermal Resistance, Junction to Ambient	R <sub>ØJA</sub>	75	75	°C/W
Thermal Resistance, Junction to Case	R <sub>ØJC</sub>	12.5	12.5	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/6" from Case for 5 Seconds	TL	260	260	°C

(1) Pulse Test: Pulse Width = 300ms. Duty Cycle  $\leq$  2%.

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

## Quality Semi-Conductors

## electrical characteristics (T<sub>C</sub> = 25°C) (unless otherwise specified)

CHARACTERISTIC		SYMBOL	MIN	TYP	MAX	UNIT
off characteristics <sup>(1)</sup>						
Collector-Emitter Voltage I <sub>C</sub> = 10mA)	D41K1,3 D41K2,4	VCEO	-30 -50	_		Volts
Collector Cut-off Current (V <sub>CE</sub> = Rated V <sub>CES</sub> )		ICES	_	_	5	μA
Emitter Cutoff Current (V <sub>EB</sub> = -13V)		IEBO	_	-	-0.1	μA
DC Current Gain (I <sub>C</sub> = -200mA, V <sub>CE</sub> = -5V)		h <sub>FE</sub>	10K	_		
(I <sub>C</sub> = -1.5A, V <sub>CE</sub> = -5V) (I <sub>C</sub> = -1A, V <sub>CE</sub> = -5V)	D41K1,2 D41K3,4	hFE	1K 1K	=		=
Collector-Emitter Saturation Voltage ( $I_C = -1.5A$ , $I_B = -3mA$ ) ( $I_C = -1.0A$ , $1_B = -2mA$ )	D41K1,2 D41K3,4	V <sub>CE(sat)</sub>		_	1.5 1.5	Volts V
Base-Emitter Saturation Voltage ( $I_C = -1.5A$ , $I_B = -3mA$ ) ( $I_C = -1A$ , $I_B = -2mA$ )	D41K1,2	V <sub>BE(sat)</sub>	_	_	2.5	Volts

### dynamic characteristics

Collector Capacitance (V <sub>CE</sub> = -10V, f = 1MHz)	Ссво		9	15	pF
Current-Gain — Bandwidth Product (I <sub>C</sub> = -20mA, V <sub>CE</sub> = -5V)	f <sub>T</sub>	_	100	-	MHz

(1) Pulse Test: PW  $\leq$  300ms Duty Cycle  $\leq$  2%.





FIG. 2 TYPICAL CCBO vs. VOLTAGE

